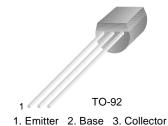


KSP55/56

Amplifier Transistor

- Collector-Emitter Voltage: V_{CEO}=KSP55: 60V KSP56: 80V
- Collector Power Dissipation: P_C (max) =625mW
- Complement to KSP05/06



PNP Epitaxial Silicon Transistor

Absolute Maximum Ratings T_a=25°C unless otherwise noted

| Symbol | Parameter | Value | Units |
|------------------|-----------------------------|-----------|-------|
| V_{CBO} | Collector-Base Voltage | | |
| | : KSP55 | -60 | V |
| | : KSP56 | -80 | V |
| V _{CEO} | Collector-Emitter Voltage | | |
| | : KSP55 | -60 | V |
| | : KSP56 | -80 | V |
| V _{CEO} | Emitter-Base Voltage | -4 | V |
| I _C | Collector Current | -500 | mA |
| P _C | Collector Power Dissipation | 625 | mW |
| T _J | Junction Temperature | 150 | °C |
| T _{STG} | Storage Temperature | -55 ~ 150 | °C |

Electrical Characteristics T_a =25°C unless otherwise noted

| Symbol | Parameter | Test Condition | Min. | Max. | Units |
|-----------------------|---------------------------------------|---|------|-------|-------|
| BV _{CEO} | * Collector-Emitter Breakdown Voltage | | | | |
| | : KSP55 | $I_C = -1 \text{mA}, I_B = 0$ | -60 | | V |
| | : KSP56 | | -80 | | |
| BV _{EBO} | Emitter-Base Breakdown Voltage | $I_E = -100 \mu A, I_C = 0$ | -4 | | V |
| I _{CBO} | Collector Cut-off Current | | | | |
| | : KSP55 | $V_{CB} = -60V, I_{E} = 0$ | | -0.1 | μΑ |
| | : KSP56 | $V_{CB} = -80V, I_{E} = 0$ | | -0.1 | μΑ |
| I _{CEO} | Collector Cut-off Current | V _{CE} = -60V, I _B =0 | | -0.1 | μΑ |
| h _{FE} | DC Current Gain | $V_{CE} = -1V, I_{C} = -10mA$ | 50 | | |
| · - | | $V_{CE} = -1V, I_{C} = -100 \text{mA}$ | 50 | | |
| V _{CE} (sat) | Collector-Emitter Saturation Voltage | I _C = -100mA, I _B = -10mA | | -0.25 | V |
| V _{BE} (on) | Base-Emitter On Voltage | V _{CE} = -1V, I _C = -100mA | | -1.2 | V |
| f _T | Current Gain Bandwidth Product | V _{CE} = -2V, I _C = -10mA f=100MHz | 50 | | MHz |

^{*} Pulse Test: PW≤300μs, Duty Cycle≤2%

Typical Characteristics

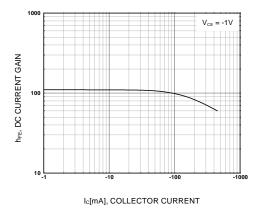


Figure 1. DC current Gain

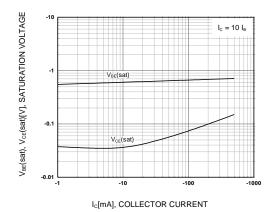


Figure 2. Collector-Emitter Saturation Voltage Base-Emitter Saturation Voltage

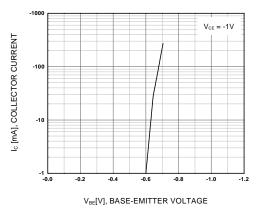


Figure 3. Base-Emitter On Voltage

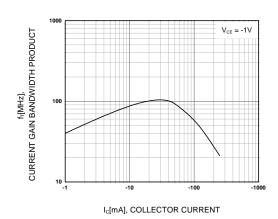
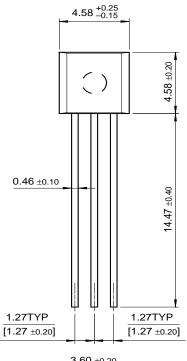


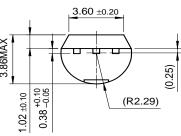
Figure 4. Current Gain Bandwidth Product

TO-92





0.38 +0.10 -0.05



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